CdSe-sensitized inorganic–organic heterojunction solar cells: The effect of molecular dipole interface modification and surface passivation

Yong Hui Lee [a,b,1], Sang Hyuk Im [a,1], Jeong Ah Chang [a], Jong-Heun Lee [b], Sang Il Seok [a,*]

[a] KRICT-EPFL Global Research Laboratory, Advanced Materials Division, Korea Research Institute of Chemical Technology, 141 Gajeong-ro, Yuseong-gu, Daejeon 305-600, Republic of Korea
[b] Department of Materials Science and Engineering, Korea University, Anam-Dong, Sungbuk-Gu, Seoul 136-713, Republic of Korea

ARTICLE INFO

ABSTRACT

CdSe-sensitized heterojunction solar cells composed of mesoscopic TiO_2/CdSe/P3HT (poly-3-hexylthiophene) were constructed, and the negative molecular dipole of 4-methoxybenzenethiol (MBT) and the ZnS passivation layer were used as interface modifiers to improve device performance. Through the interface modification between TiO_2/CdSe and P3HT using MBT and by ZnS surface passivation, the power conversion efficiency of the modified solar cell was greatly enhanced from 1.02% to 1.62% under 1 sun illumination.

1. Introduction

Solar energy conversion systems have received considerable attention because solar energy is abundant, renewable, and clean. Conventional silicon solar cells would be placed by dye-sensitized solar cells (D-SSCs) [1] and bulk heterojunction-organic solar cells (BHJ-OSCs) [2], which are considered representative next-generation solar cells. D-SSCs are unique because they are composed of a mesoscopic photoanode, sensitizer, and hole transporting material, which serve as an electron conductor, light absorber, and redox electrolyte. The separate role of each component enables D-SSCs to maintain good performance because the possibility of recombination is very low. A considerable enhancement in device efficiency has been successfully demonstrated by the extremely enlarged interfacial area in both D-SSCs and BHJ-OSCs. Therefore, it is desirable to use morphologically pre-developed porous architecture

to attain high device efficiency. In addition, the use of a solid-state hole conductor instead of a conventional liquid redox electrolyte can prevent potential electrolyte leakage and enable the fabrication of flexible devices. Accordingly, low-cost and highly efficient solar cells can be developed by combining the porous architecture of the electron conductor in D-SSCs and the solid-state hole conductor in BHJ-OSCs.

Inorganic semiconductors and quantum dots have been considered promising alternatives to conventional organic dyes owing to their unique properties such as a high extinction coefficient, intrinsically large dipole moment, convenient bandgap tunability, multiple exciton generation, and good stability [3]. Therefore, metal chalcogenides such as CdS(e) [4–7], PbS(e) [8–10], and Sb_2S_3 [11–15] have been used as inorganic semiconductor sensitizers. Recently, we reported on the fabrication of highly efficient Sb_2S_3-sensitized inorganic–organic heterojunction solar cells [11,12]. However, efficient solid-state CdSe-sensitized heterojunction solar cells have not been reported, despite the development of efficient liquid-type CdSe-sensitized photoelectrochemical solar cells [16] and the fact that

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* Corresponding author. Fax: +82 42 861 4151.
  E-mail address: seoksi@krict.re.kr (S.I. Seok).
  [1] These two authors have equally contributed to this study.

the bulk bandgap of CdSe is similar to that of Sb_2S_3. This might be attributed to the upset or insufficient difference in energy level between CdSe and TiO_2 to attain an efficient charge injection process.

Shalom et al. [17] suggested that a molecular dipole attached to an inorganic semiconductor surface can increase the energy levels toward the vacuum level, causing the electron injection to become more favorable. Chi et al. [18] recently reported that molecular dipole treatment is still effective in solid-state CdS/CdSe-co-sensitized solar cells composed of mesoscopic TiO_2/CdS-CdSe/spiro-MeO-TAD (2,2′,7,7′-tetrakis (N,N-di-p-methoxyphenylamine)-9,9′-spirobifluorene). Through molecular dipole treatment using an inorganic semiconductor sensitizer and TiO_2 surface passivation, they could attain a 0.88% power conversion efficiency at 1 sun illumination (AM 1.5G 100 mW/cm^2). Unlike the wide bandgap spiro-MeOTAD hole conductor, P3HT (poly-3-hexylthiophene) can absorb visible light and generate charge carriers. It has been reported that the generated charge carriers in the P3HT donor can be transported to the CdSe acceptor in hybrid solar cells [19] and transported to TiO_2 through a CdS intermediate [20]. To improve the device performance of CdSe-sensitized solar cells, here, we fabricated CdSe-sensitized heterojunction solar cells composed of mesoscopic TiO_2/CdSe/P3HT as an electron conductor/inorganic semiconductor sensitizer/hole conducting dye layer and treated the CdSe surface with a molecular dipole.

2. Experimental

2.1. Device fabrication

A 100-nm-thick dense TiO_2 blocking layer (bl-TiO_2) was deposited on an F-doped SnO_2 (FTO, Pilkington, TEC 8) glass substrate by spray pyrolysis deposition of 20 mM of titanium diisopropoxide bis(acetylacetonate) (Aldrich) solution at 450 °C to prevent the hole conductor from being in direct contact with the FTO substrate. A 1-μm-thick mesoscopic TiO_2 layer (particle size = ~50 nm, anatase) [13,21] was then screen printed onto a bl-TiO_2/FTO substrate and heat-treated at 500 °C for 30 min in air. It should be noted that the transparent FTO glass substrate was cleaned ultrasonically in successive baths in acetone and ethanol and then dried under airflow before use. The CdSe sensitizer was prepared by the successive ionic layer adsorption and reaction (SILAR) process. For deposition, TiO_2 films were successively immersed into 0.03 M $Cd(NO_3)_2$ in ethanol and then into 0.03 M Se^{2-} precursor for 30 s each [13,22]. After cation dipping, the film was washed with ethanol, dried with an air blower, and dipped in anion precursor. This SILAR process was repeated 8 (CdSe-8), 10 (CdSe-10), and 12 (CdSe-12) times. Selenium precursor [23] was prepared by reducing SeO_2 with $NaBH_4$ in ethanol under an Ar atmosphere. All processes were carried out in an Ar-purged glove box. For negative molecular dipole interface modification, 1 mL of 0.1 M 4-methoxy-benzenethiol (MBT) solution in ethanol was dropped onto mesoscopic CdSe/TiO_2 films and spin-coated for 30 s at 3000 rpm. For ZnS surface passivation, the ZnS layer was

formed on a CdSe/TiO_2(/MBT) film by successive dipping into 0.05 M $Zn(NO_3)_2$ and 0.05 M Na_2S aqueous solution via 1 cycle of the SILAR process. The P3HT (98% regioregular, Rieke) solution (15 mg/1 mL dichlorobenzene) was spincoated at 2500 rpm for 60 s. PEDOT:PSS (AI 4083, Clevios) in methanol (1/2 v/v) was then spincoated at 2500 rpm for 60 s and dried at 90 °C for 30 min in a vacuum oven. Finally, a Au counter electrode was deposited by thermal evaporation. The active area of the device was fixed at 0.16 cm^2.

2.2. Device characterization

The current density–voltage (J–V) characteristics of the cells were measured under 100 mW/cm^2 illumination using a solar simulator (Newport Co. Oriel Class A, 91195A) with a Keithley 2420 Source Meter® and a calibrated Si-reference cell (certified by NREL). The external quantum efficiency (EQE) was measured using a fully computerized home-designed system consisting of a light source (Newport 300 W Xenon lamp 66902) aligned with a monochromator (Newport Cornerstone™ 260) and a multimeter (Keithley 2001). J–V characteristics of the cells were measured using a metal mask of 0.16 cm^2.

3. Results and discussion

The schematic energy band diagram of the CdSe-sensitized inorganic–organic heterojunction solar cell is shown in Fig. 1(a). The CdSe nanoparticles generate electron–hole pairs by illuminated external light, and the generated electrons (holes) are injected into TiO_2 (P3HT). At the same time, the P3HT also absorbs the light and generates electron–hole pairs; the electrons from these pairs can be cascade-transferred to TiO_2 through the CdSe intermediate. It should be noted that P3HT has the dual function of hole conductor and light absorber; thus, it was named a hole conducting dye. Generally, the sizes of the CdSe nanoparticles produced by the SILAR process are polydispersed; consequently, a diverse energy bandgap associated with the CdSe sensitizer will coexist in the device, as shown in Fig. 1(a). The smaller CdSe nanoparticles can more energetically inject electrons into TiO_2 than the larger ones owing to the quantum size effect. Therefore, a negative molecular dipole interface treatment at the CdSe/P3HT interface should be desirable to more energetically inject electrons from CdSe to TiO_2, The SEM cross-sectional image of the CdSe-sensitized heterojunction solar cell shown in Fig. 1(b) demonstrates that the thickness of the mesoscopic TiO_2 electron conductor is ~1 μm. It should be noted that, unlike in liquid photoelectrochemical solar cells, the thickness of the mesoscopic TiO_2 layer is limited by the pore-filling problem associated with hole transporting materials in solid-state solar cells. Therefore, we used ~1-μm-thick TiO_2 film that had been previously confirmed not to have a pore-filling problem [13]. A typical TEM image of CdSe nanoparticles deposited on mesoscopic TiO_2 film is shown in Fig. 1(c). This image clearly indicates that most of the surfaces of the TiO_2 nanoparticles are well covered by CdSe nanoparticles. The TiO_2 (~50 nm) and CdSe (~5 nm)